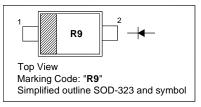
SILICON EPITAXIAL SCHOTTKY BARRIER DIODE

Applications

• High speed switching

PINNING

PIN	DESCRIPTION
1	Cathode
2	Anode



Absolute Maximum Ratings (T_a = 25 °C)

Parameter	Symbol	Value	Unit
Maximum (Peak) Reverse Voltage	V_{RM}	25	V
Reverse Voltage	V _R	20	V
Average Forward Current	Io	300	mA
Maximum (Peak) Forward Current	I _{FM}	700	mA
Power Dissipation	P _{tot}	200	mW
Junction Temperature	T _J	125	°C
Storage Temperature Range	Ts	- 55 to + 125	°C

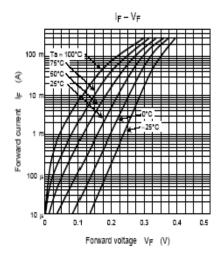
Characteristics at T_a = 25 °C

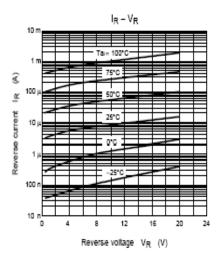
onarcione ar ia = 0		_	_	_
Parameter	Symbol	Тур.	Max.	Unit
Forward Voltage at I _F = 300 mA	V _F	-	0.45	V
Reverse Current at $V_R = 20 \text{ V}$	I _R	-	50	μΑ
Total Capacitance at f = 1 MHz	Ст	46	-	pF

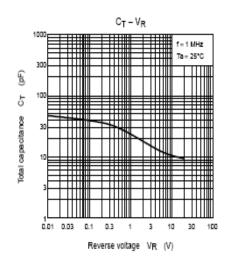


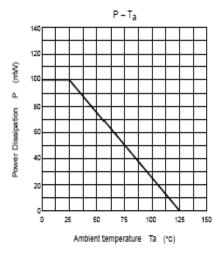
















(Subsidiary of Sino-Tech International Holdings Limited, a company listed on the Hong Kong Stock Exchange, Stock Code: 724)







ISO/TS 16949 : 2002 ISO 14001 : 2004 ISO 9001 : 2000 Certificate No. 05103 Certificate No. 7116 Certificate No. 0506098

PACKAGE OUTLINE

Plastic surface mounted package; 2 leads

SOD-323

